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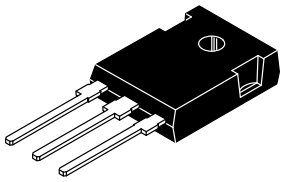
Complementary Silicon Plastic Power Transistors

Specifically designed for power audio output, or high power drivers in audio amplifiers.

- DC Current Gain Specified up to 8.0 Amperes at Temperature
- All On Characteristics at Temperature
- High SOA: 20 A, 18 V, 100 ms
- TO–247AE Package

NPN
MJW21192
PNP
MJW21191

8.0 AMPERES
POWER TRANSISTORS
COMPLEMENTARY
SILICON
150 VOLTS
100 WATTS



CASE 340K–01
TO–247AE

MAXIMUM RATINGS

Rating	Symbol	MJW21191 MJW21192	Unit
Collector–Emitter Voltage	V_{CEO}	150	Vdc
Collector–Base Voltage	V_{CB}	150	Vdc
Emitter–Base Voltage	V_{EB}	5.0	Vdc
Collector Current — Continuous — Peak	I_C	8.0 16	Adc
Base Current	I_B	2.0	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	100 0.65	Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.65	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	50	°C/W

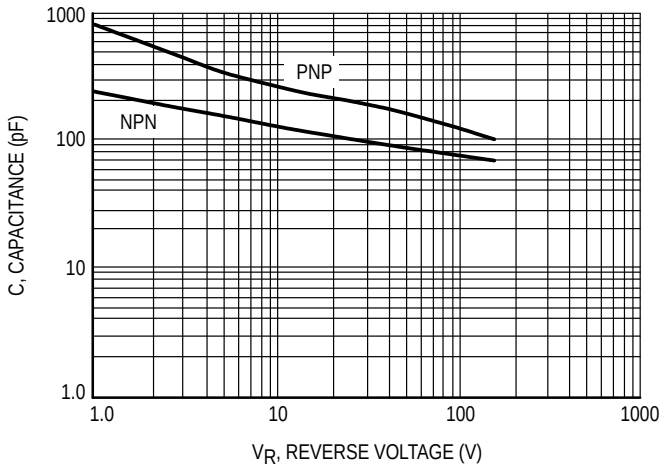


Figure 1. Typical Capacitance @ 25°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (1) (I_C = 10 mAdc, I_B = 0)	$V_{CEO(sus)}$	150	—	Vdc
Collector Cutoff Current (V_{CB} = 250 Vdc, I_E = 0)	I_{CES}	—	10	μAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)	I_{EBO}	—	10	μAdc
ON CHARACTERISTICS (1)				
DC Current Gain (I_C = 4.0 Adc, V_{CE} = 2.0 Vdc) (I_C = 8.0 Adc, V_{CE} = 2.0 Vdc)	h_{FE}	15 5.0	— —	— 100
Collector–Emitter Saturation Voltage (I_C = 4.0 Adc, I_B = 0.4 Adc) (I_C = 8.0 Adc, I_B = 1.6 Adc)	$V_{CE(sat)}$	— —	1.0 2.0	Vdc
Base–Emitter On Voltage (I_C = 4.0 Adc, V_{CE} = 2.0 Vdc)	$V_{BE(on)}$	—	2.0	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain — Bandwidth Product (2) (I_C = 1.0 Adc, V_{CE} = 10 Vdc, f_{test} = 1.0 MHz)	f_T	4.0	—	MHz

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) $f_T = |h_{fe}| \bullet f_{test}$.

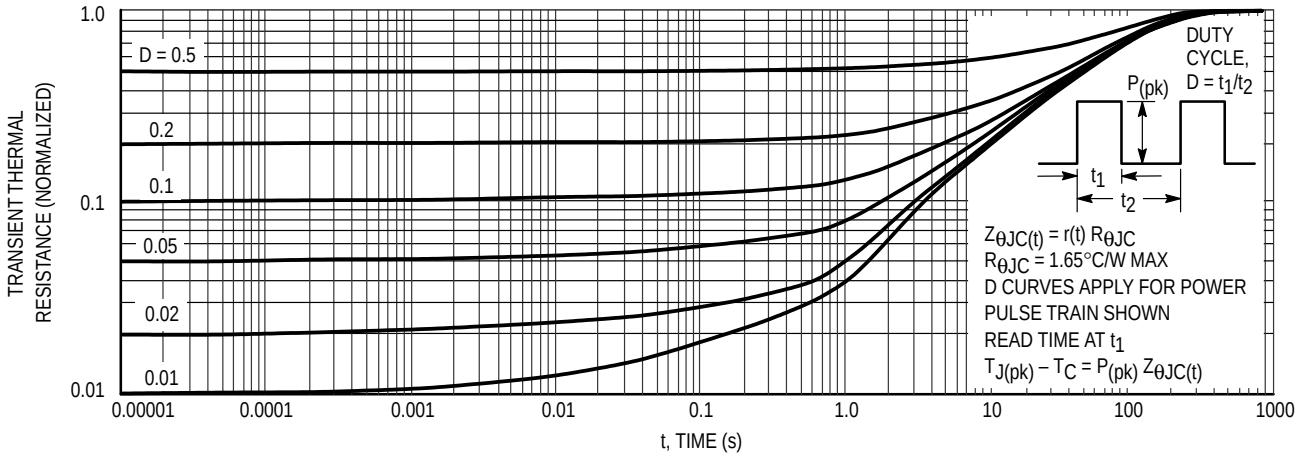


Figure 2. Thermal Response

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation then the curves indicate.

The data of Figures 3 and 4 is based on $T_{J(pk)} = 150°C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 150°C$. $T_{J(pk)}$ may be calculated from the data in Figure 2. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

NPN — MJW21192

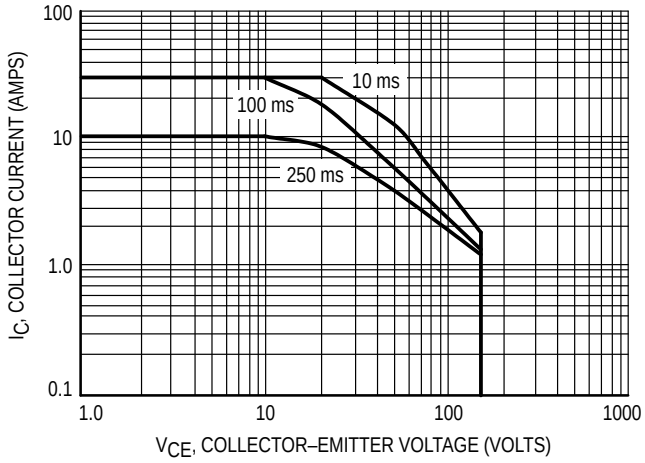


Figure 3. NPN — MJW21192 Safe Operating Area

PNP — MJW21191

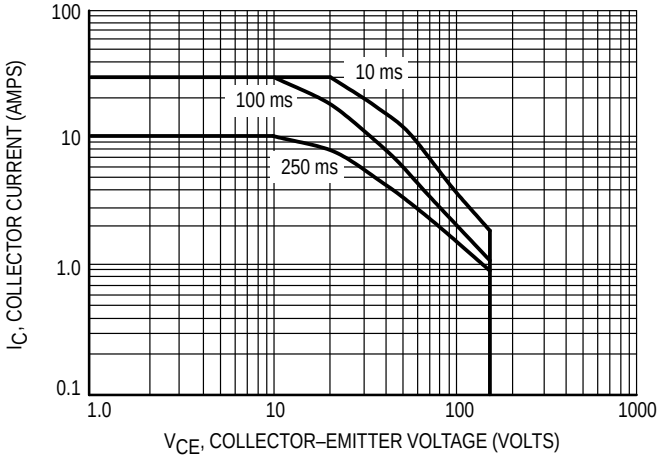


Figure 4. PNP — MJW21191 Safe Operating Area

TYPICAL CHARACTERISTICS

NPN — MJW21192

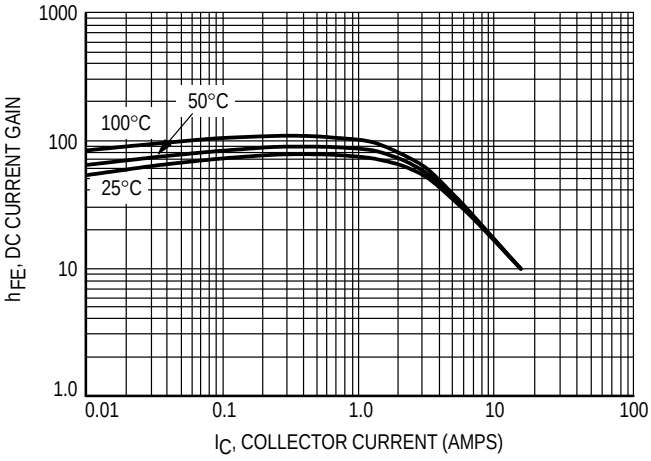


Figure 5. NPN — MJW21192 V_{CE} = 2.0 V DC Current Gain

PNP — MJW21191

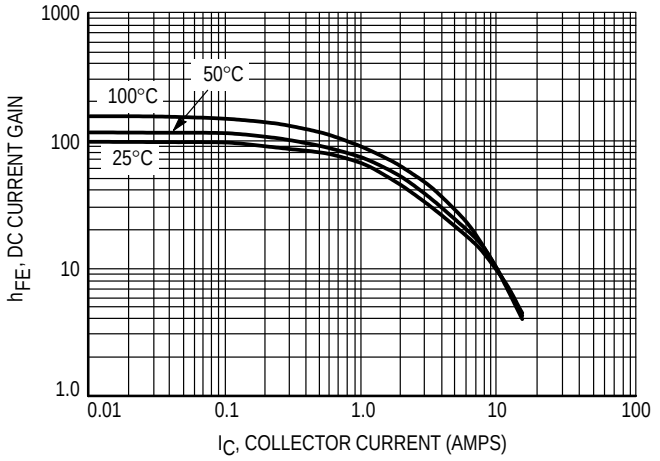


Figure 6. PNP — MJW21191 V_{CE} = 2.0 V DC Current Gain

NPN — MJW21192

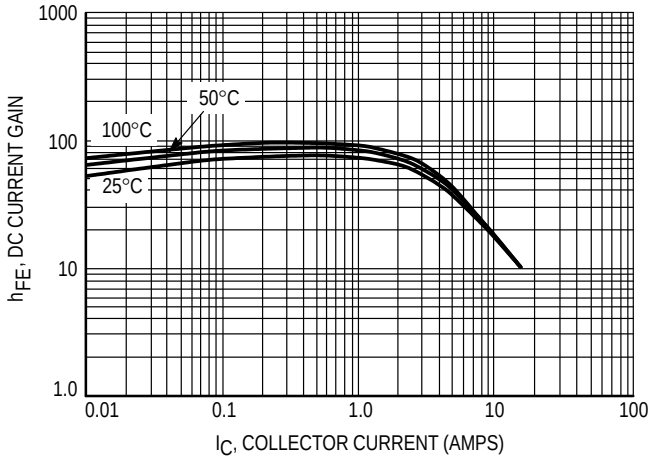


Figure 7. NPN — MJW21192
V_{CE} = 5.0 V DC Current Gain

PNP — MJW21191

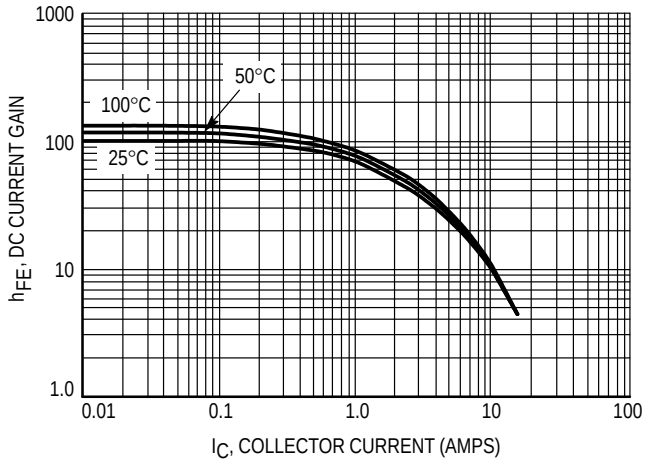


Figure 8. PNP — MJW21191
V_{CE} = 5.0 V DC Current Gain

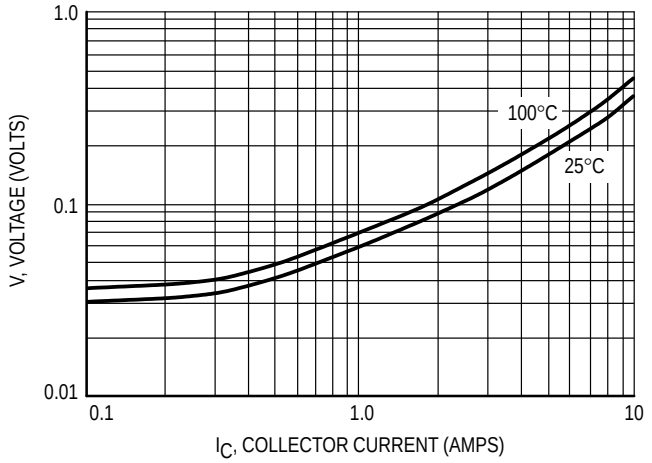


Figure 9. NPN — MJW21192
$V_{CE(sat)}$ I_C/I_B = 5.0

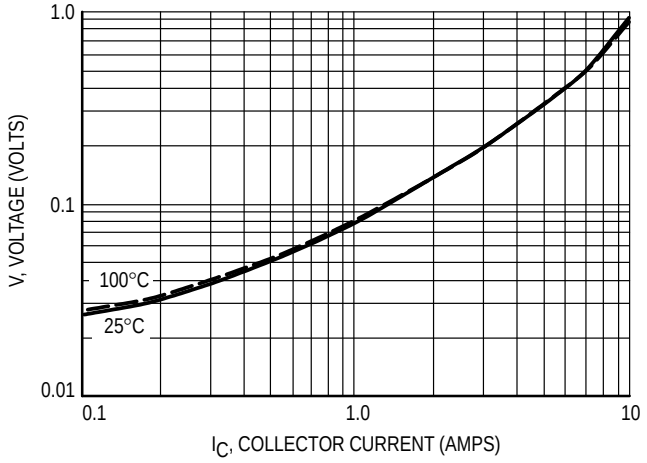


Figure 10. PNP — MJW21191
$V_{CE(sat)}$ I_C/I_B = 5.0

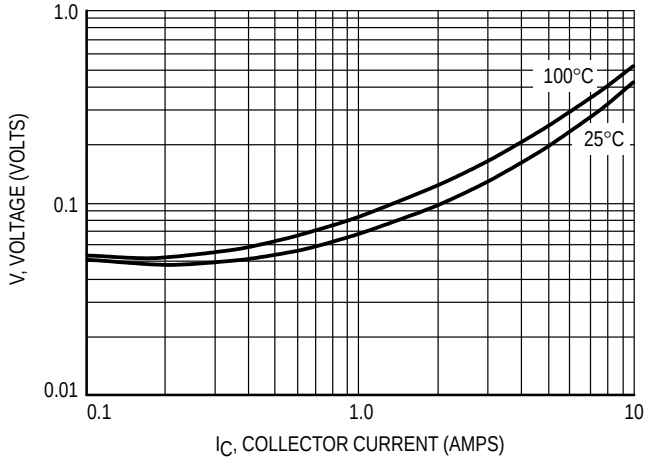


Figure 11. NPN — MJW21192
$V_{CE(sat)}$ I_C/I_B = 10

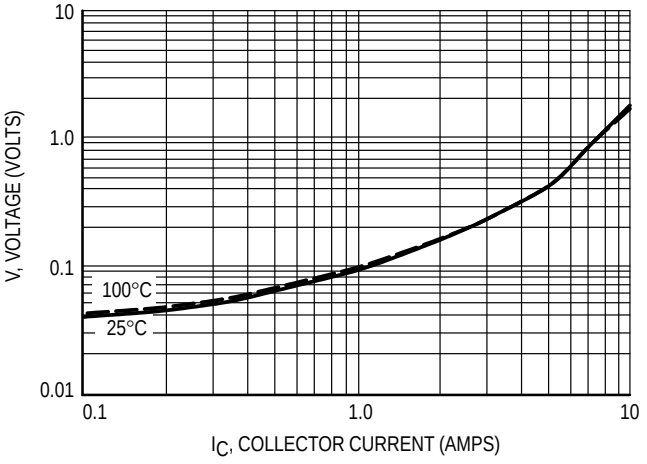


Figure 12. PNP — MJW21191
$V_{CE(sat)}$ I_C/I_B = 10

NPN — MJW21192

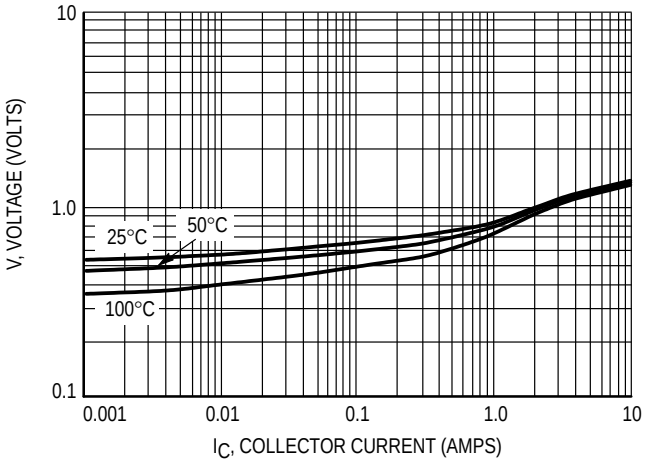


Figure 13. NPN — MJW21192
V_{CE} = 2.0 V $V_{BE(on)}$ Curve

PNP — MJW21191

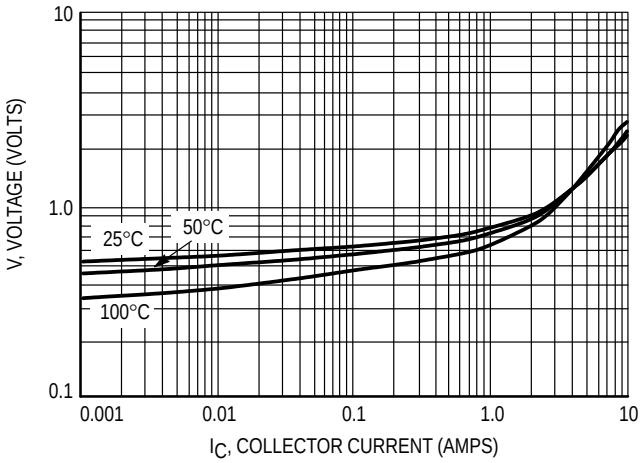
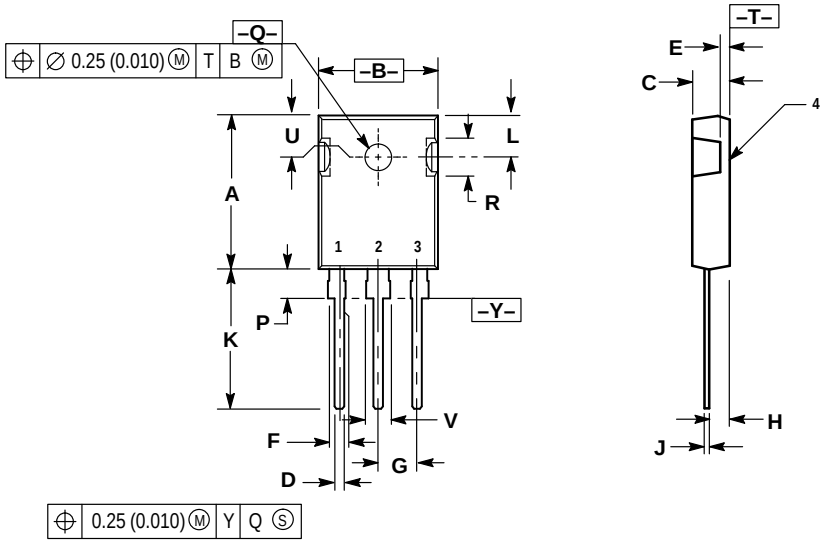


Figure 14. PNP — MJW21191
V_{CE} = 2.0 V $V_{BE(on)}$ Curve

PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	19.7	20.3	0.776	0.799
B	15.3	15.9	0.602	0.626
C	4.7	5.3	0.185	0.209
D	1.0	1.4	0.039	0.055
E	1.27 REF		0.050 REF	
F	2.0	2.4	0.079	0.094
G	5.5 BSC		0.216 BSC	
H	2.2	2.6	0.087	0.102
J	0.4	0.8	0.016	0.031
K	14.2	14.8	0.559	0.583
L	5.5 NOM		0.217 NOM	
P	3.7	4.3	0.146	0.169
Q	3.55	3.65	0.140	0.144
R	5.0 NOM		0.197 NOM	
U	5.5 BSC		0.217 BSC	
V	3.0	3.4	0.118	0.134

CASE 340K–03
(TO–247AE)
ISSUE A

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